L Number	Hits	Search Text	DB	Time stamp
1	281	257/68	USPAT	2004/05/26 11:17
2	826	257/288	USPAT	2004/05/26 11:17
3	3238	257/296	USPAT	2004/05/26 11:17
4	1313	257/314	USPAT	2004/05/26 11:17
5	2308	257/315	USPAT	2004/05/26 11:17
6	550	257/377	USPAT	2004/05/26 11:17
7	402	257/380	USPAT	2004/05/26 11:17
8	1041	257/382	USPAT	2004/05/26 11:17
9	1171	257/412	USPAT	2004/05/26 11:18
10	649	257/413	USPAT	2004/05/26 11:18
-	1	10/064383	USPAT	2004/05/26 10:20
-	1		USPAT	2004/05/26 10:28
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-	Ó	(electron adj capturing) and memory and device and width	USPAT	2004/05/26 10:23
		and conductive and tunnel and oxide and spacer and sidewall		200 11 001 20 101 20
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		dielectric and nitride and silicon and polysilicon and		
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